

1 Characteristics

Table 2: Absolute maximum ratings (limiting values), $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter		Value	Unit
$I_{T(RMS)}$	RMS on-state current (180 ° conduction angle)		$T_c = 119\text{ }^{\circ}\text{C}$	40 A
$I_{T(AV)}$	Average on-state current (180 ° conduction angle)	$T_c = 120\text{ }^{\circ}\text{C}$	25	A
		$T_c = 125\text{ }^{\circ}\text{C}$	22	
		$T_c = 128\text{ }^{\circ}\text{C}$	20	
I_{TSM}	Non repetitive surge peak on-state current		$t_p = 8.3\text{ ms}$	A
			$t_p = 10\text{ ms}$	
I^2t	I^2t value for fusing		$t_p = 10\text{ ms}$	648 A ² s
di/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, $t_r \leq 100\text{ ns}$		$f = 60\text{ Hz}$	100 A/ μ s
V_{DRM}/V_{RRM}	Repetitive peak off-state voltage		$T_j = 150\text{ }^{\circ}\text{C}$	600 V
V_{DSM}/V_{RSM}	Non repetitive surge peak off-state voltage		$t_p = 10\text{ ms}$	$V_{DRM}/V_{RRM} + 100$ V
I_{GM}	Peak gate current	$t_p = 20\text{ }\mu\text{s}$	$T_j = 150\text{ }^{\circ}\text{C}$	4 A
$P_{G(AV)}$	Average gate power dissipation		$T_j = 150\text{ }^{\circ}\text{C}$	1 W
V_{RGM}	Maximum peak reverse gate voltage			5 V
T_{stg}	Storage junction temperature range			-40 to +150 $^{\circ}\text{C}$
T_j	Maximum operating junction temperature			-40 to +150 $^{\circ}\text{C}$
T_L	Maximum lead temperature soldering during 10 s			260 $^{\circ}\text{C}$

Table 3: Electrical characteristics ($T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Conditions		Value	Unit
I_{GT}	$V_D = 12\text{ V}$, $R_L = 33\text{ }\Omega$	Max.	15	mA
V_{GT}		Max.	1.3	V
V_{GD}	$V_D = V_{DRM}$, $R_L = 3.3\text{ k}\Omega$	$T_j = 150\text{ }^{\circ}\text{C}$	Min.	0.15 V
I_H	$I_T = 500\text{ mA}$, gate open		Max.	60 mA
I_L	$I_G = 1.2 \times I_{GT}$		Max.	80 mA
dV/dt	$V_D = 402\text{ V}$, gate open	$T_j = 150\text{ }^{\circ}\text{C}$	Min.	500 V/ μ s
t_{gt}	$I_T = 80\text{ A}$, $V_D = 600\text{ V}$, $I_G = 100\text{ mA}$, $(dI_G/dt)_{\text{max}} = 0.2\text{ A}/\mu\text{s}$		Typ.	1.9 μ s
t_q	$V_D = 402\text{ V}$, $I_T = 40\text{ A}$, $V_R = 25\text{ V}$, $dV_D/dt = 50\text{ V}/\mu\text{s}$, $(dI_G/dt)_{\text{max}} = 30\text{ A}/\mu\text{s}$	$T_j = 150\text{ }^{\circ}\text{C}$	Typ.	85 μ s

Table 4: Static characteristics

Symbol	Test conditions			Value	Unit
V_{TM}	$I_{TM} = 80\text{ A}$, $t_p = 380\text{ }\mu\text{s}$	$T_j = 25\text{ }^\circ\text{C}$	Max.	1.6	V
V_{TO}	Threshold voltage	$T_j = 150\text{ }^\circ\text{C}$	Max.	0.85	
R_D	Dynamic resistance	$T_j = 150\text{ }^\circ\text{C}$	Max.	10	m Ω
I_{DRM} , I_{RRM}	$V_D = V_{DRM} = V_{RRM}$	$T_j = 25\text{ }^\circ\text{C}$	Max.	10	μA
		$T_j = 150\text{ }^\circ\text{C}$		6	mA

Table 5: Thermal parameters

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case (DC)	Max.	0.8	$^\circ\text{C/W}$
$R_{th(j-a)}$	Junction to ambient (DC)	Typ.	60	

1.1 Characteristics (curves)

Figure 1: Maximum average power dissipation versus average on-state current

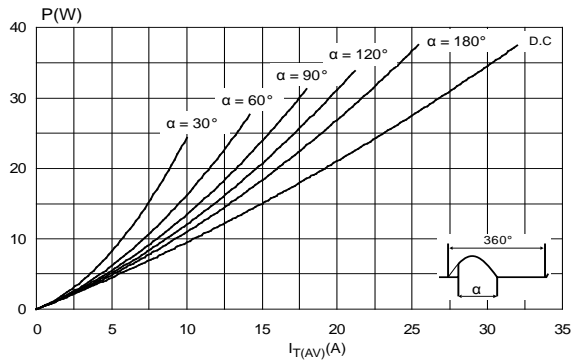


Figure 2: Average and DC on-state current versus case temperature

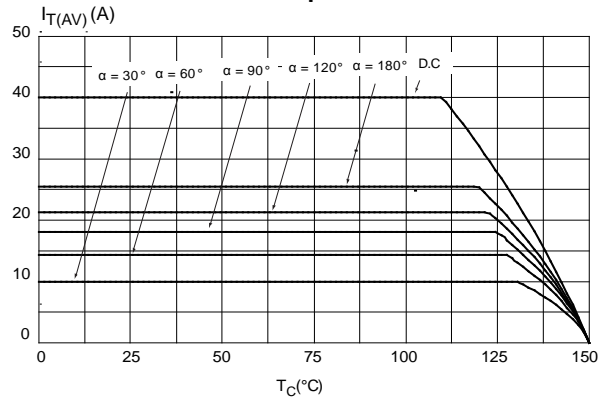


Figure 3: Average and D.C. on state current versus ambient temperature

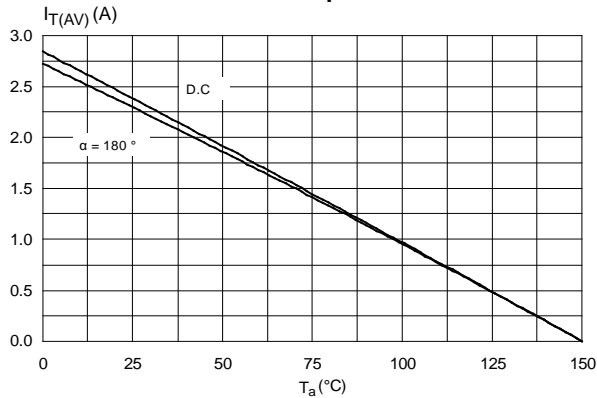


Figure 4: Relative variation of thermal impedance versus pulse duration

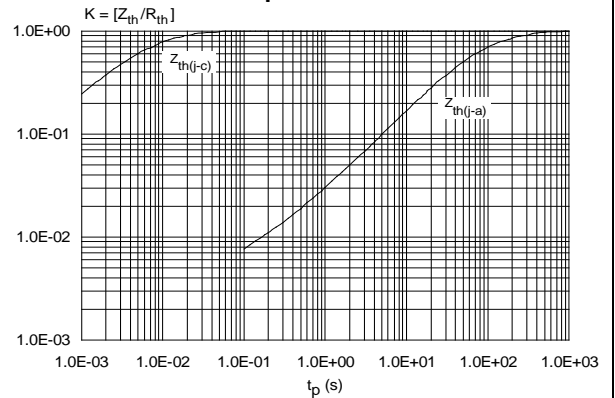


Figure 5: Relative variation of gate trigger current and gate voltage versus junction temperature (typical values)

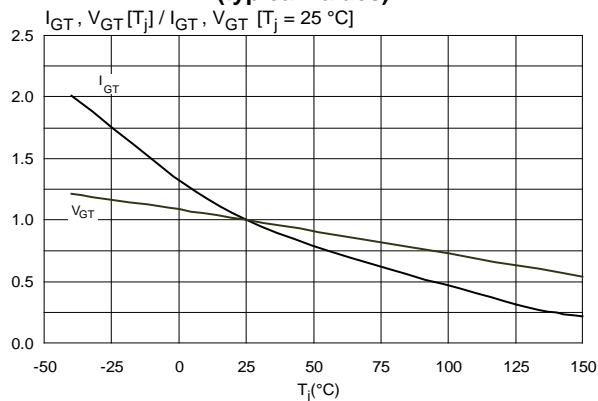
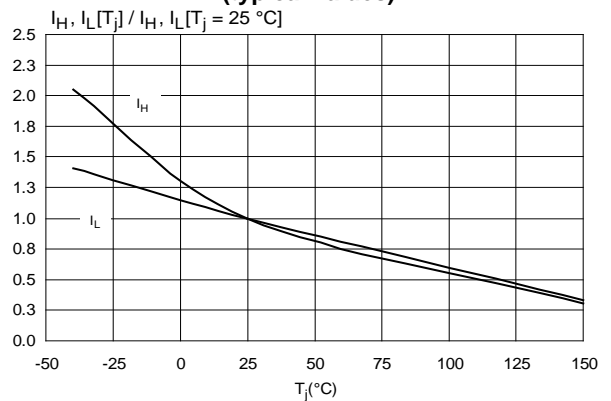
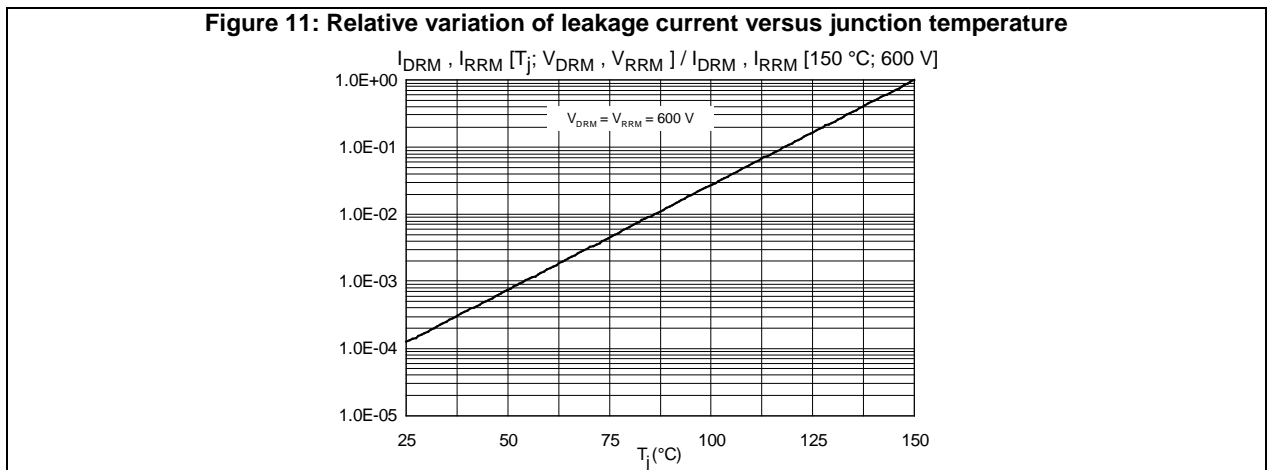
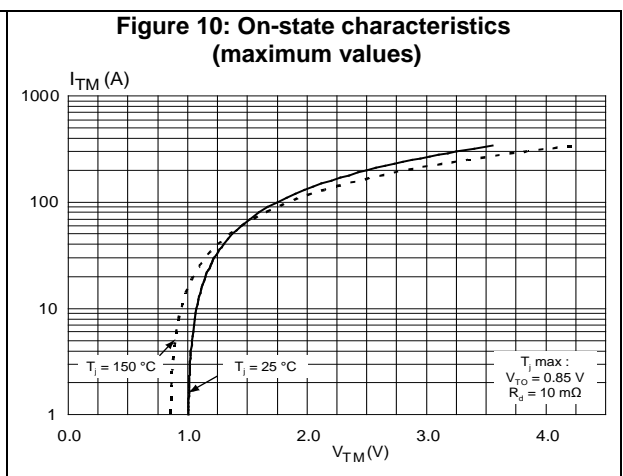
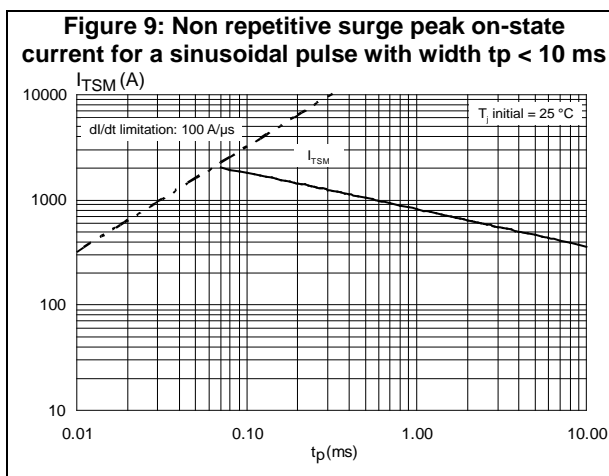
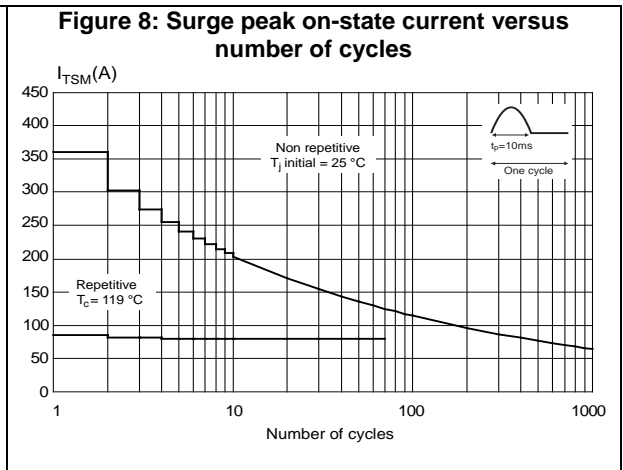
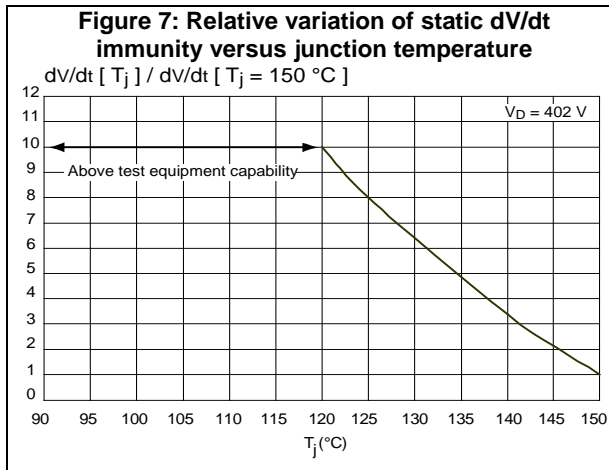


Figure 6: Relative variation of holding and latching current versus junction temperature (typical values)





2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

- Epoxy meets UL94, V0
- Lead-free, halogen-free package

2.1 TO-220AB package information

Figure 12: TO-220AB package outline

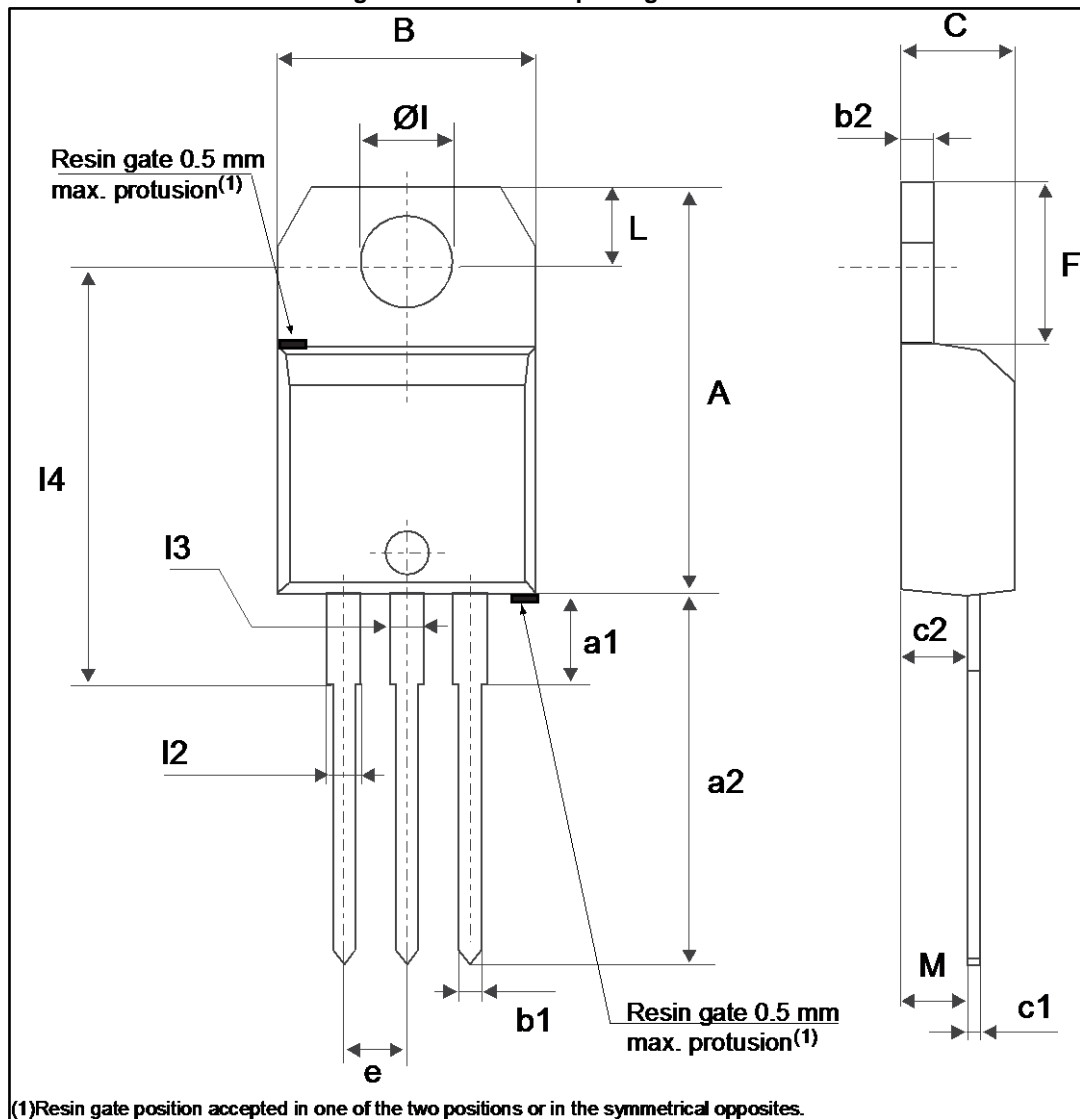


Table 6: TO-220AB package mechanical data

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.20		15.90	0.5984		0.6260
a1		3.75			0.1476	
a2	13.00		14.00	0.5118		0.5512
B	10.00		10.40	0.3937		0.4094
b1	0.61		0.88	0.0240		0.0346
b2	1.23		1.32	0.0484		0.0520
C	4.40		4.60	0.1732		0.1811
c1	0.49		0.70	0.0193		0.0276
c2	2.40		2.72	0.0945		0.1071
e	2.40		2.70	0.0945		0.1063
F	6.20		6.60	0.2441		0.2598
ØI	3.73		3.88	0.1469		0.1528
l4	15.8	16.40	16.80	0.6220	0.6457	0.6614
L	2.65		2.95	0.1043		0.1161
l2	1.14		1.70	0.0449		0.0669
l3	1.14		1.70	0.0449		0.0669
M		2.60			0.1024	

3 Ordering information

Figure 13: Ordering information scheme

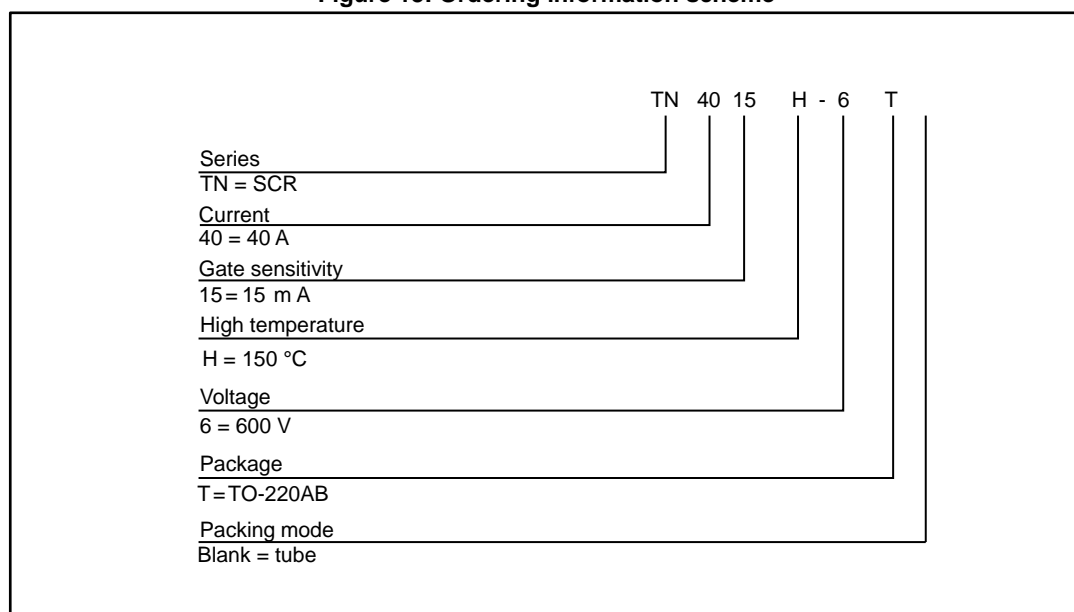


Table 7: Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
TN4015H-6T	TN4015H6	TO-220AB	2.3 g	50	Tube

4 Revision history

Table 8: Document revision history

Date	Revision	Changes
08-Sep-2016	1	Initial release.

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